

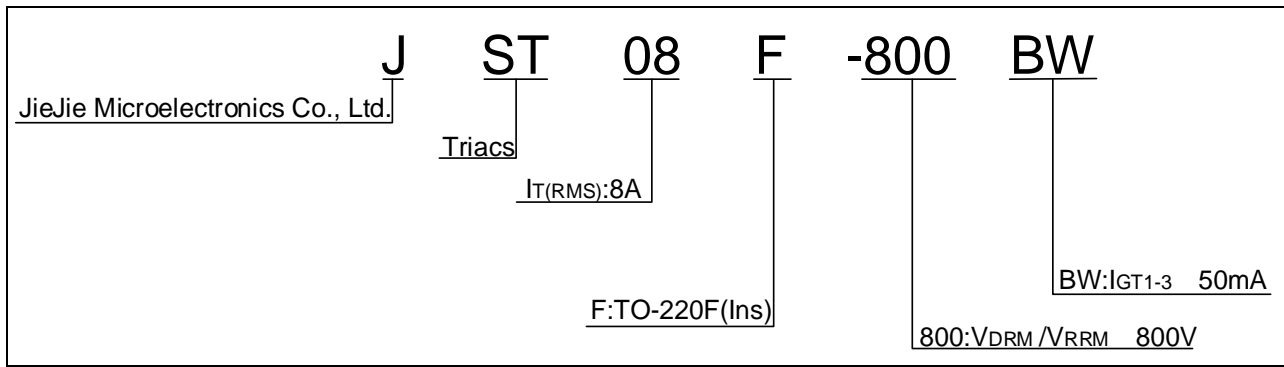


Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	2.5	kV

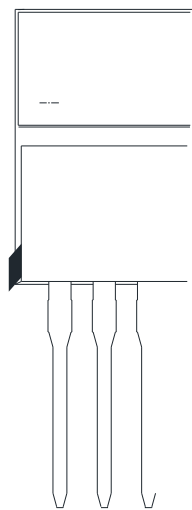
**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V$ $R_L=33$	- -	MAX.	50	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				90	

## ORDERING INFORMATION

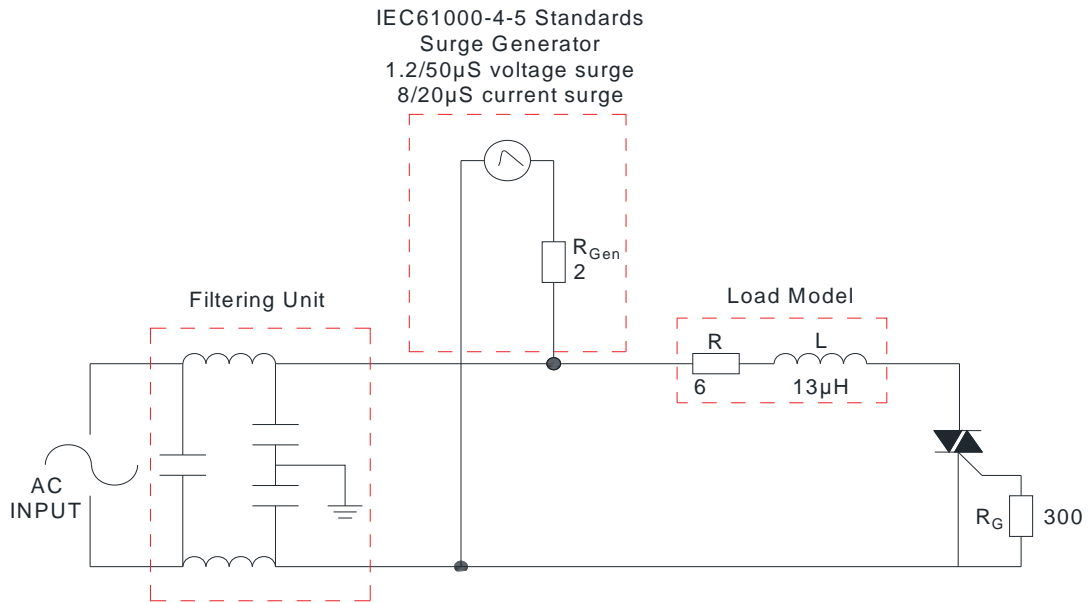


## MARKING



**JST08F-800BW**

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards








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